

VLSI System Design

Jin-Fu Li

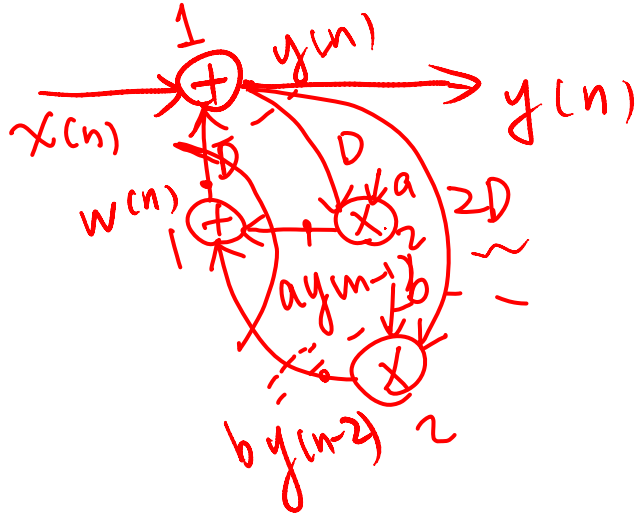
Advanced Reliable Systems (ARES) Laboratory

Department of Electrical Engineering

National Central University

Jhongli, Taiwan

Data flow graph (DFG)



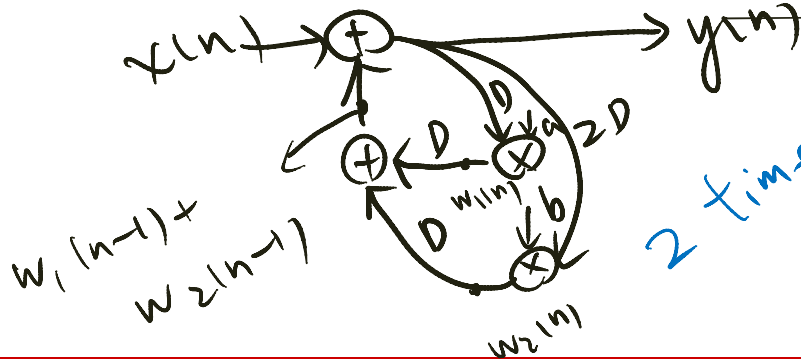
3 ~~to~~ time units

$$y(n) = w(n-1) + x(n)$$

$$\underline{w(n)} = ay^{(n-1)} + by^{(n-2)}$$

$$y(n) = ay(n-2) + by(n-3) + x(n)$$

cutset retiming



cutset

Set

$$w(n) = ay(n-1)$$

$$w_1(n) = a y(n)$$

$$w_1(n) = ay^{(n)}$$

$$w_2(n) = by^{(n-2)}$$

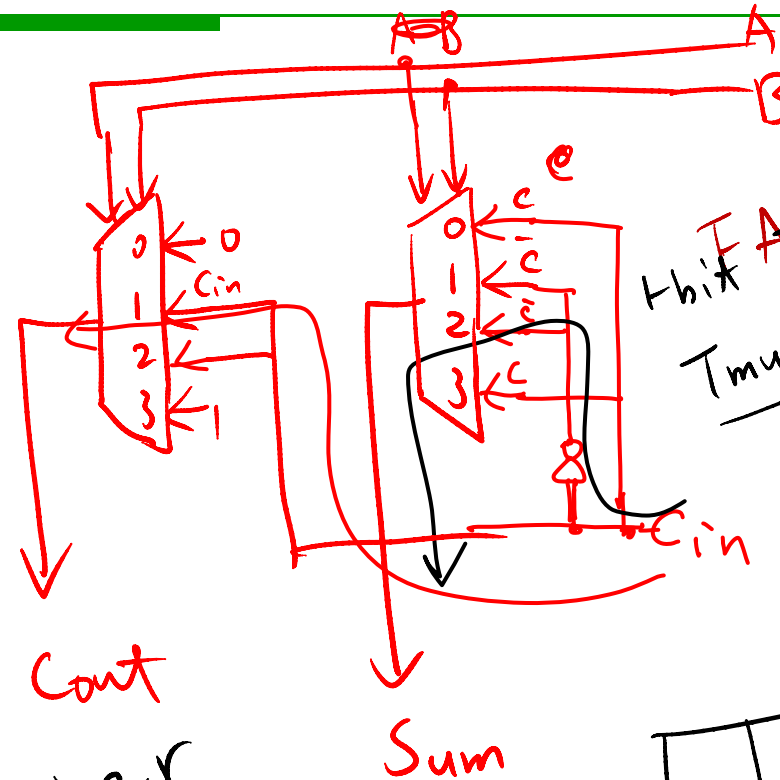
$$y(n) = w_1(n-1) + w_2(n-1) + x(n)$$

$$= ay^{(n-2)} + by^{(n-3)} + x(n)$$



Full adder

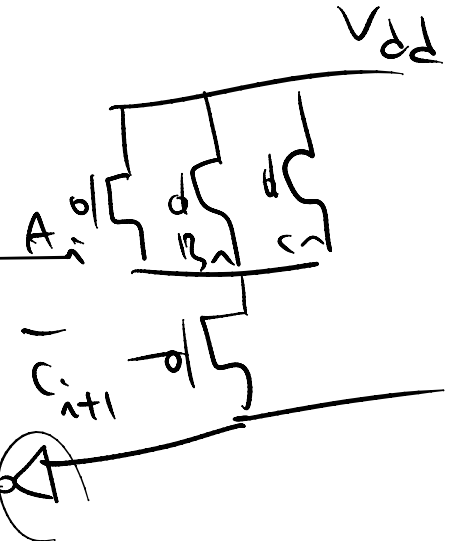
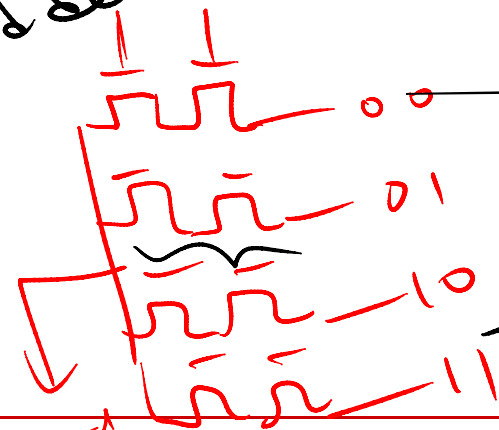
A	B	Cin	Sum	Cont
0	0	0	0	0
0	0	1	1	0
0	1	0	1	0
0	1	1	0	1
1	0	0	1	0
1	0	1	0	1
1	1	0	0	1
1	1	1	1	1

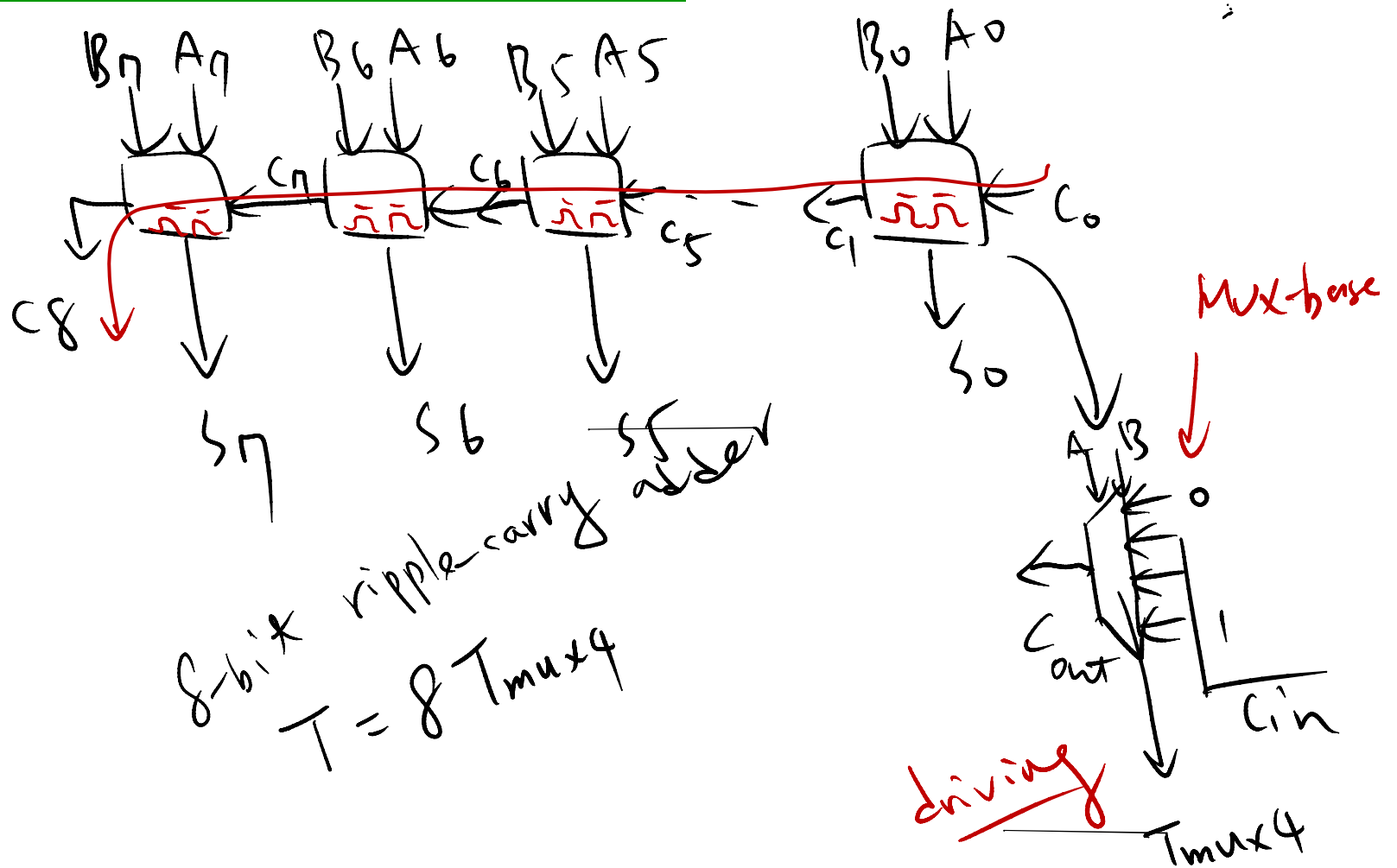


1-bit FA
 $T_{mux4} + T_{inv}$

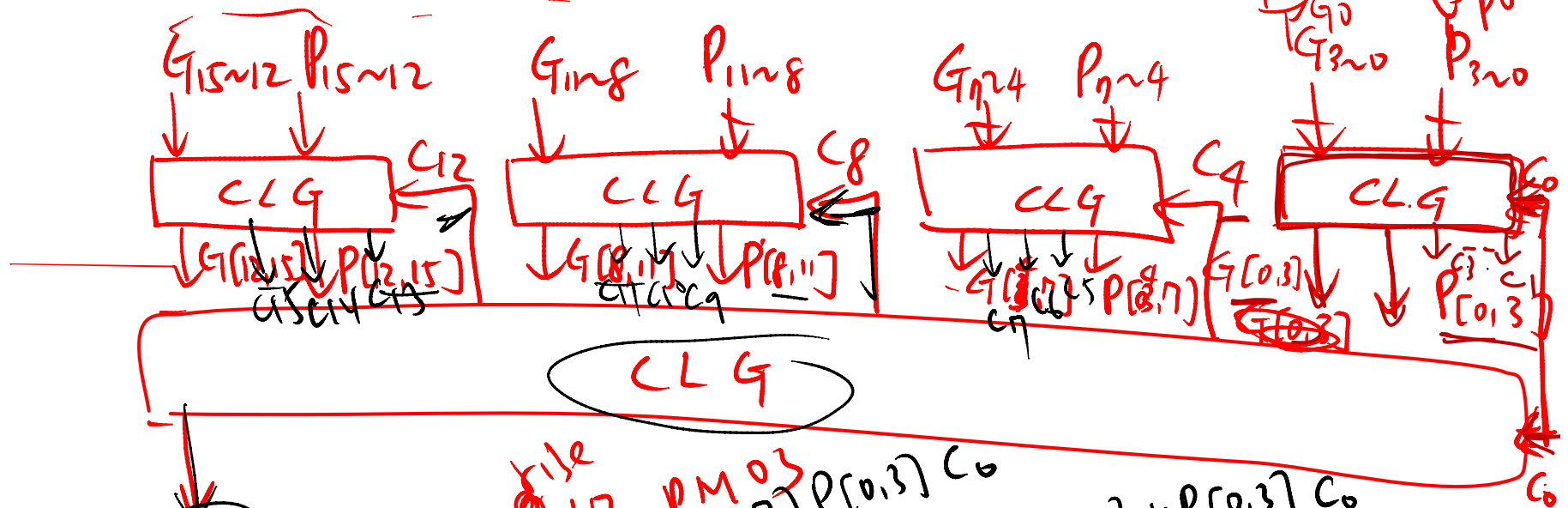
ripple-carry

adder





16-bit CLA



$$\begin{aligned}
 C_8 &= G[4:7] + G[0:3]P[4:7] + P[4:7]P[0:3]C_0 \\
 C_{16} &= G[12:15] + G[8:11]P[12:15] + P[12:15]P[8:11]P[4:7] + P[12:15]P[8:11]P[4:7]P[0:3]C_0 \\
 &= G[12:15] + G[8:11]P[12:15] + P[12:15]P[8:11]P[4:7] + P[12:15]P[8:11]P[4:7]P[0:3]C_0
 \end{aligned}$$

16-bit CLA

$$C_{i+1} = g_i + p_i C_i$$

$$G(i, i+1)$$

$$C_4 = g[0,3] + p[0,3] C_0$$

$$C_8 = G[4,7] + G[0,3] p[4,7] + p[4,7] p[0,3] C_0$$

$$C_1 = g_0 + p_0 C_0$$

$$C_2 = g_1 + g_0 p_1 + p_0 p_1 C_0$$

$$C_3 = g_2 + g_1 p_2 + g_0 p_1 p_2 + p_0 p_1 p_2 C_0$$

$$C_4 = [g_3 + g_2 p_3 + g_1 p_2 p_3 + g_0 p_1 p_2 p_3] + [p_0 p_1 p_2 p_3] C_0$$

$$p[0,3]$$

$$p_4 p_5 p_6 p_7$$

$$C_5 = g_4 + g_3 p_4 + g_2 p_3 p_4 + g_1 p_2 p_3 p_4 + g_0 p_1 p_2 p_3 p_4 + p_0 p_1 p_2 p_3 p_4 C_0$$

$$C_6 = g_5 + g_4 p_5 + g_3 p_4 p_5 + g_2 p_3 p_4 p_5 + g_1 p_2 p_3 p_4 p_5 + g_0 p_1 p_2 p_3 p_4 p_5 + p_0 p_1 p_2 p_3 p_4 p_5 C_0$$

$$C_7 = g_6 + g_5 p_6 + g_4 p_5 p_6 + g_3 p_4 p_5 p_6 + g_2 p_3 p_4 p_5 p_6 + g_1 p_2 p_3 p_4 p_5 p_6 + g_0 p_1 p_2 p_3 p_4 p_5 p_6 + p_0 p_1 p_2 p_3 p_4 p_5 p_6 C_0$$

$$C_8 = [g_7 + g_6 p_7 + g_5 p_6 p_7 + g_4 p_5 p_6 p_7] + [p_0 p_1 p_2 p_3 p_4 p_5 p_6 p_7] C_0$$

$$c_1 = g_0 + p_0 c_0$$

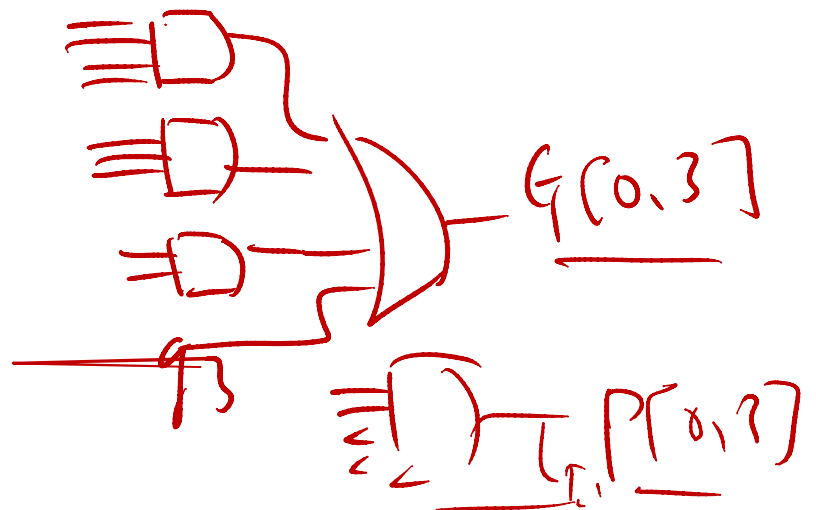
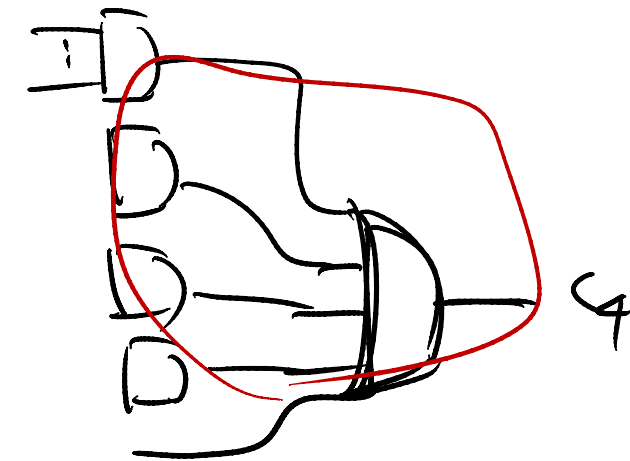
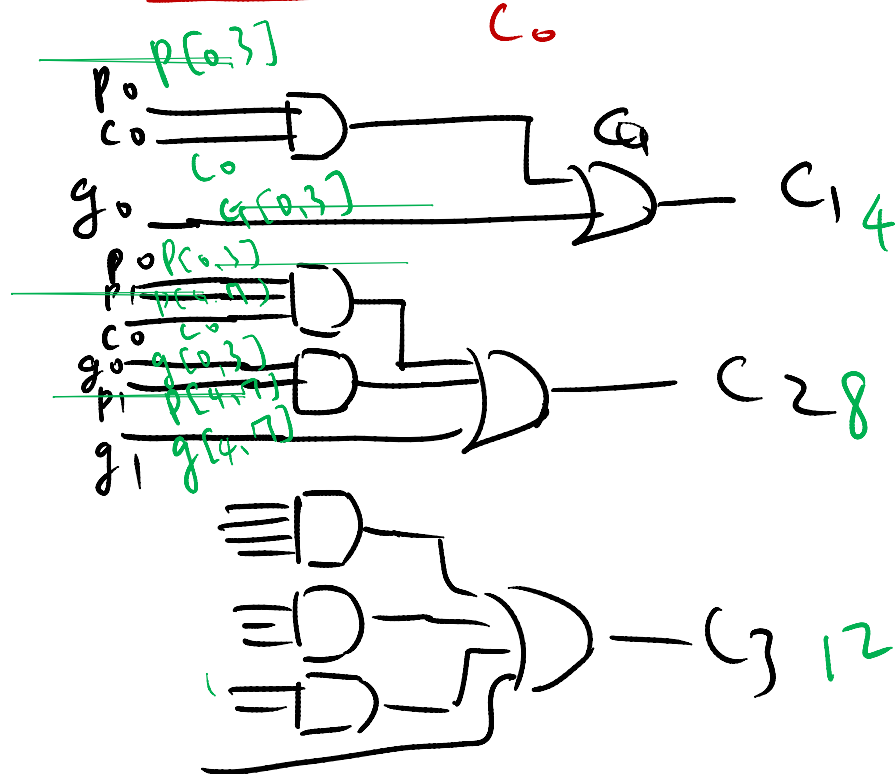
$$c_2 = g_1 + g_0 p_1 + p_0 p_1 c_0$$

$$c_3 = g_2 + g_1 p_2 + g_0 p_1 p_2 + p_0 p_1 p_2 c_0$$

$$c_4 = [g_3 + g_2 p_3 + g_1 p_2 p_3 + g_0 p_1 p_2 p_3] + [p_0 p_1 p_2 p_3] c_0$$

$$p_i = A_i \oplus B_i$$

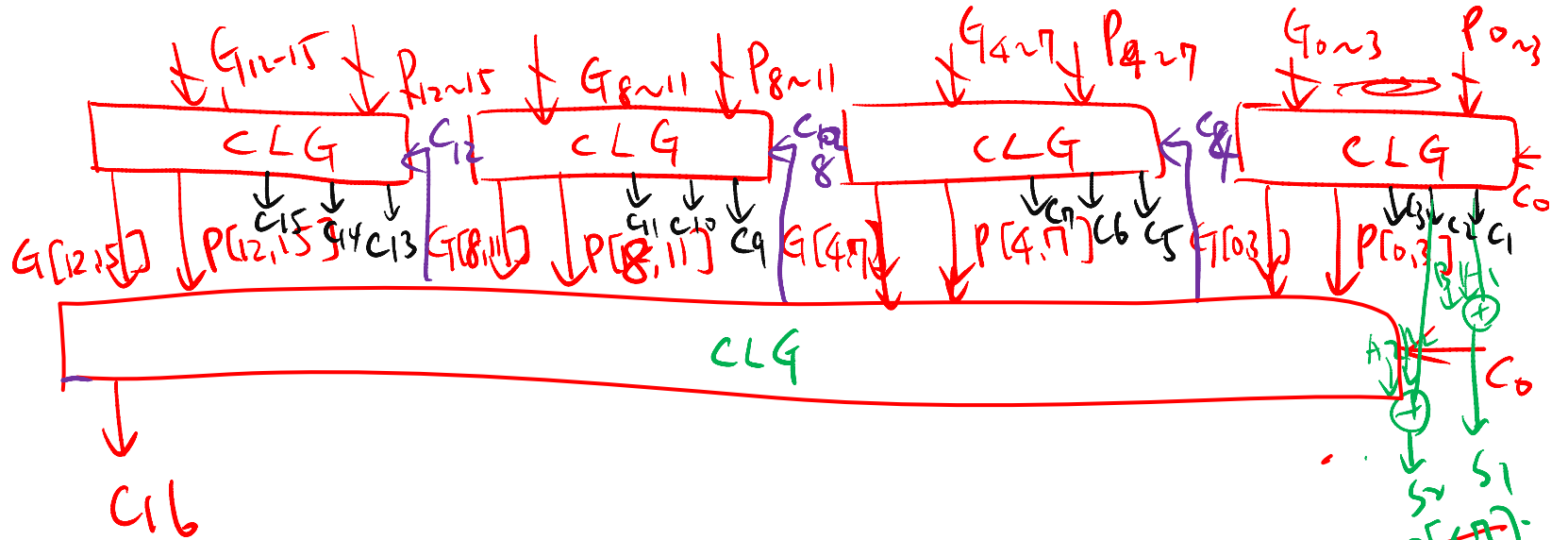
$$g_i = A_i B_i$$



11

$$S_0 = A_0 \oplus B_0 \oplus C_0$$

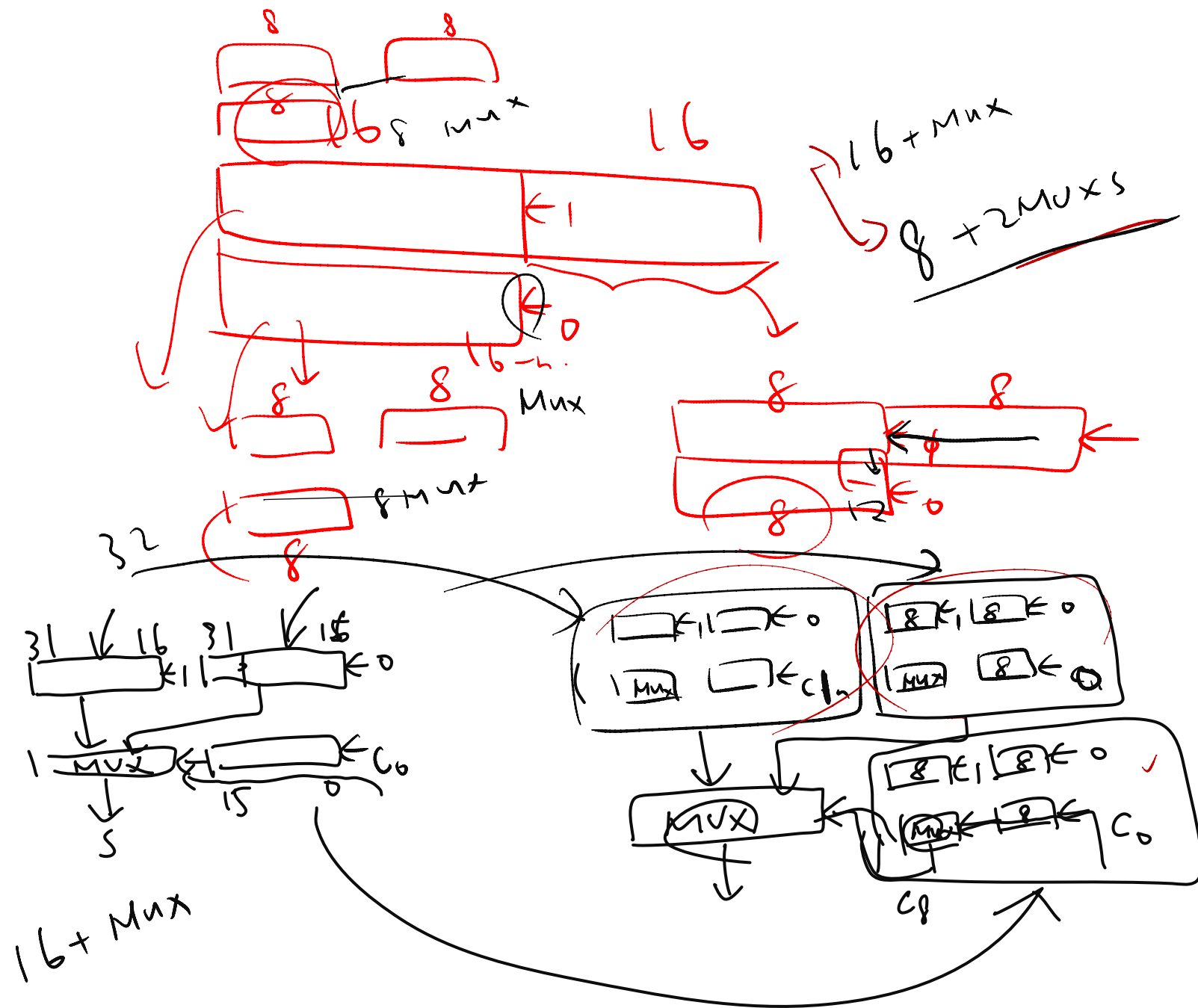
$$S_n = A_n \oplus B_n \oplus C_n$$



$$G[0,3] = g_3 + g_2p_3 + g_1p_2p_3 + g_0p_1p_2p_3$$

$$P[0,3] = p_0p_1p_2p_3$$

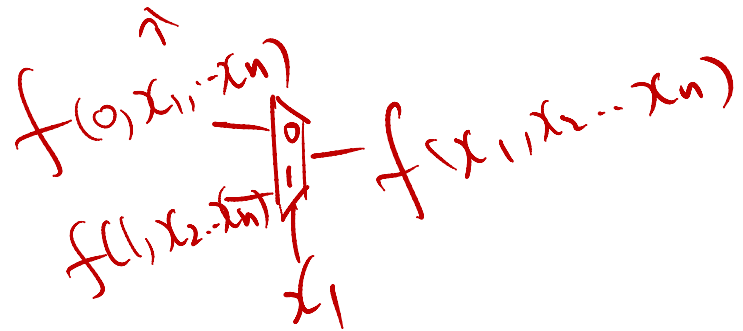
$$C_{16} = G[12,15] + G[8,11]P[12,15] + G[4,7]P[8,11]P[12,15] + G[0,3]P[4,7]P[8,11]P[12,15] + P[0,3]P[4,7]P[8,11]P[12,15]C_0$$



Shannon Expansion \rightarrow BDD Binary Decision Diagram

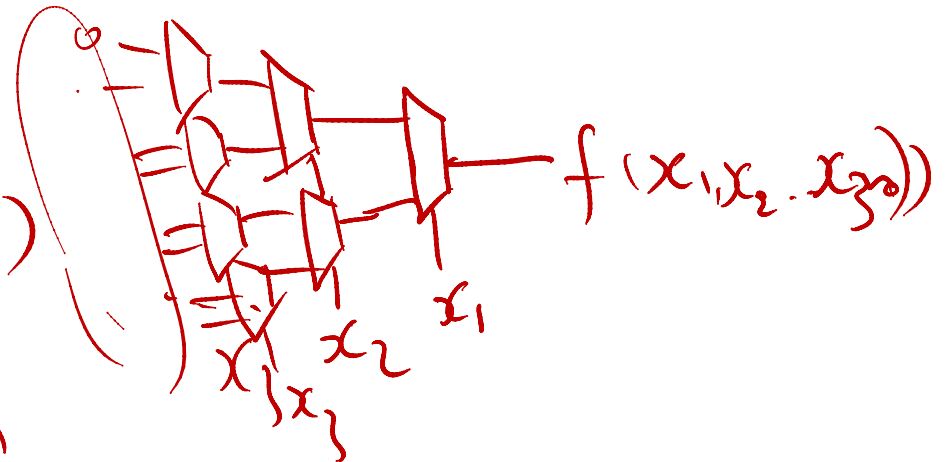
$$f(x_1, x_2, \dots, x_n) = x_1 f(1, x_2, \dots, x_n) + \bar{x}_1 f(0, x_2, \dots, x_n)$$

$$= x_1 [x_2 f(1, 1, \dots, x_n) + \bar{x}_2 f(1, 0, \dots, x_n)] + \bar{x}_1 [x_2 f(0, 1, \dots, x_n) + \bar{x}_2 f(0, 0, \dots, x_n)]$$



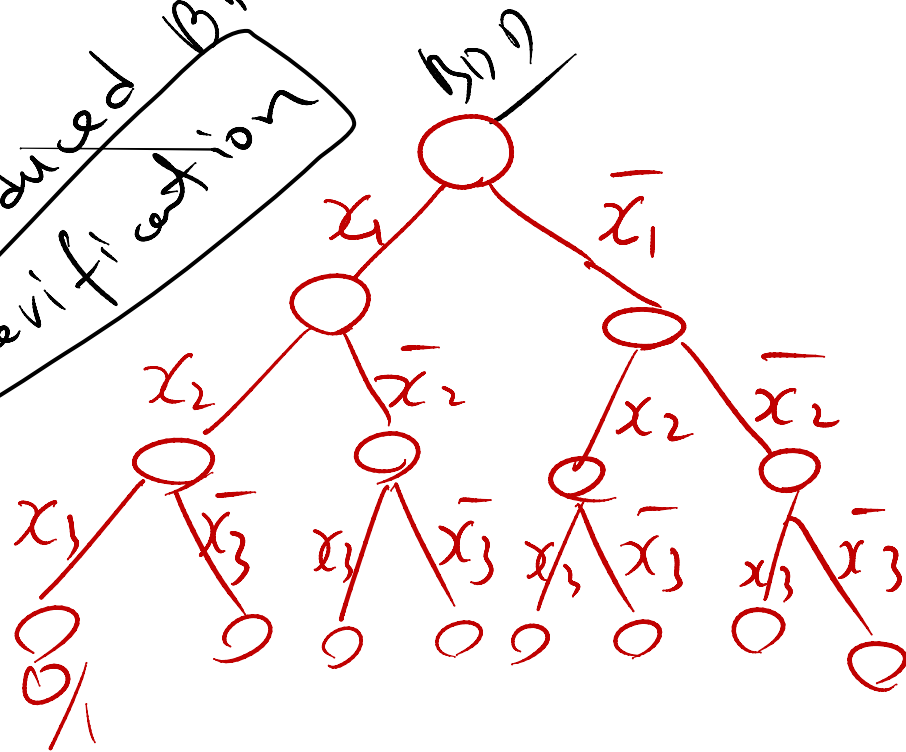
LUT + Mux + FFs

$$x_1 f(1, x_2, x_3) + \bar{x}_1 f(0, x_2, x_3)$$



Formal Verification

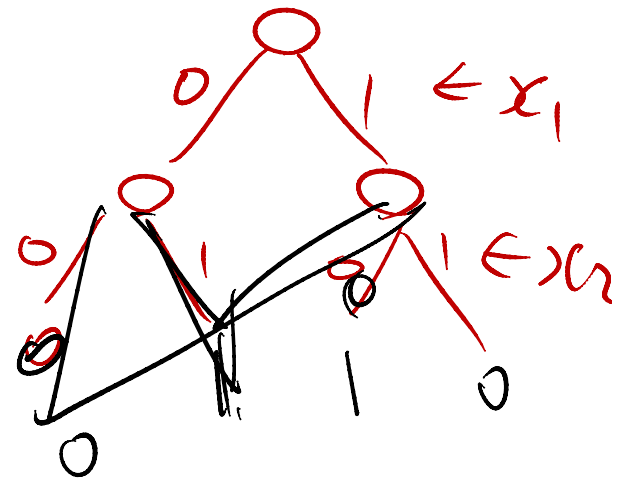
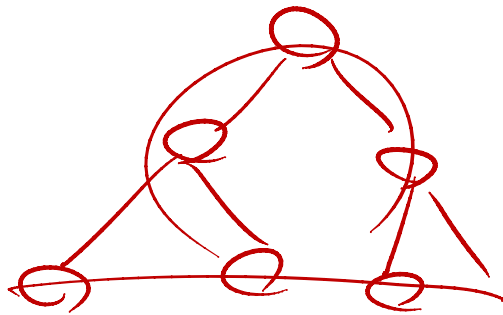
Reduced BDD



$$f(x_1, x_2) = x_1 \bar{x}_2 + \bar{x}_1 x_2$$

BDD

to R



Ternary CAM cell

"0" or "1" or "x"
 ↑ ↑ ↑
 don't care



Binary CAM cell

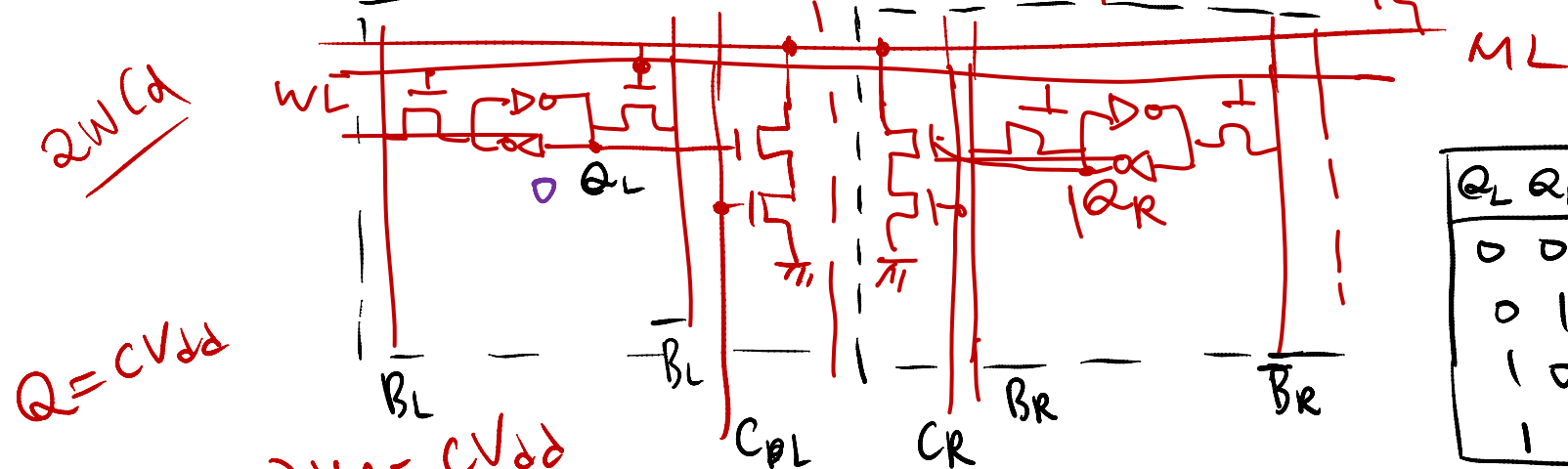
"0" or "1"

TCAM cell

depends on the cell structure

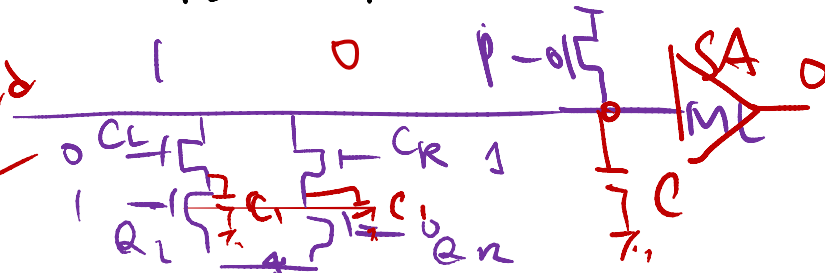
⇒ Symmetric TCAM cell & Asymmetric TCAM cell

~~Symmetric TCAM cell (NOR-type)~~



Q_L	Q_R	Ternary state
0	0	X
0	1	0
1	0	1
1	1	illegal

$(WC_1 + C)V_f = CV_{dd}$
 $V_f = \frac{C}{WC_1 + C} V_{dd}$

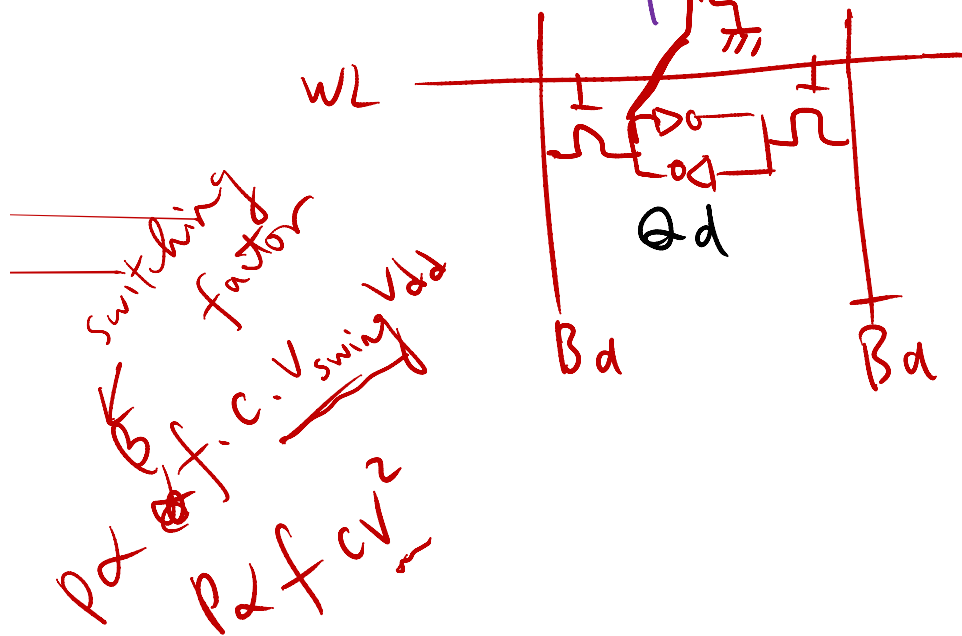


C_L	C_R	
0	0	X
0	1	1
1	0	0
1	1	illegal

Asymmetric TCAM cell (NOR-type)

low-power

Q_u	Q_d	ternary state
0/1	0	X
0	1	0
1	1	1



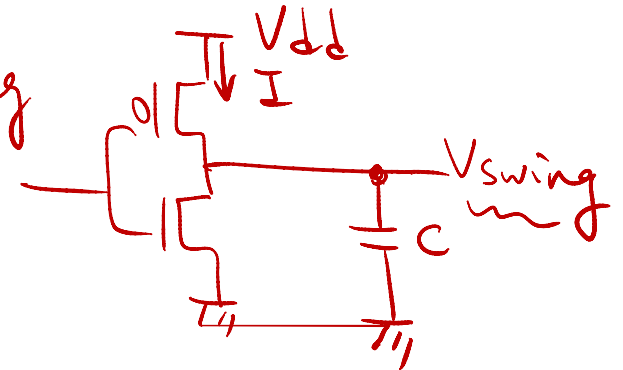
140.115. x x	140.115. -
140.115. (X). X	M0
140.111. x x	M1
140.112. x x	M2
140.113. x x	M3
140.116. x x	M4

recharge

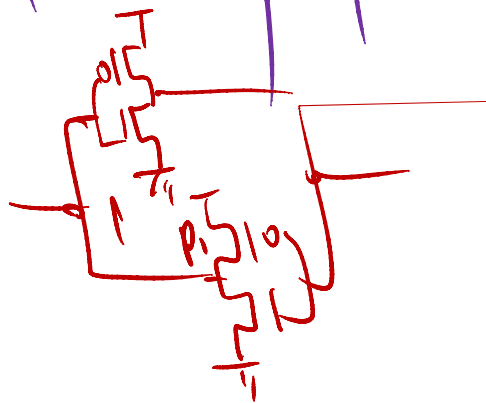
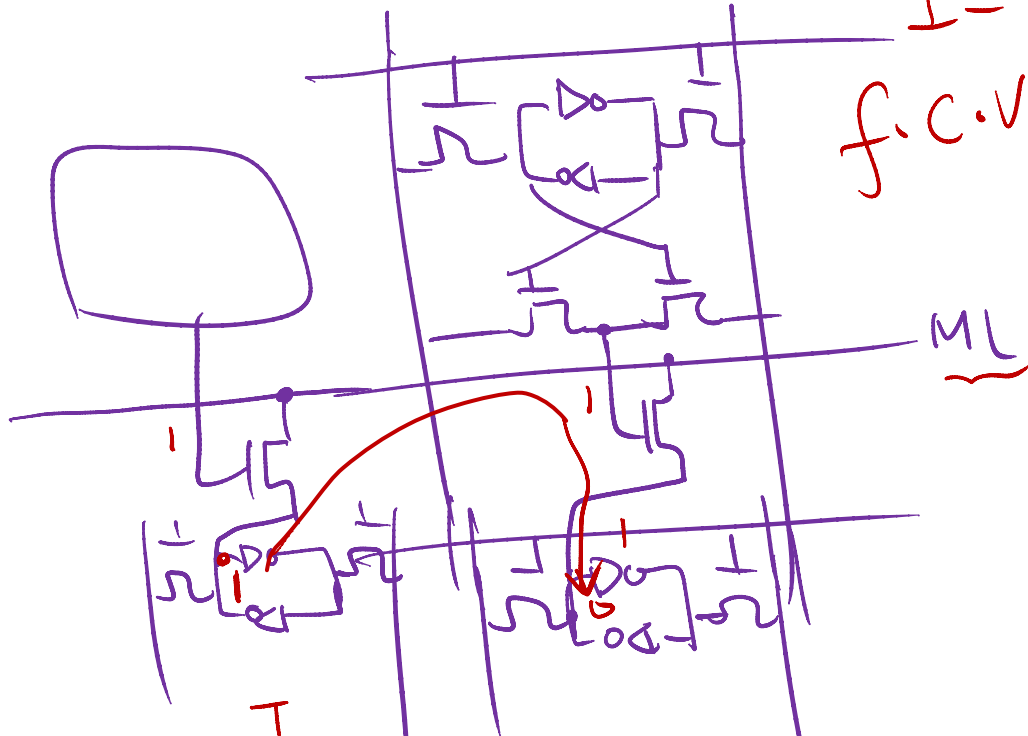
$$Q = CV = IT \quad P = IV_{dd}$$

$$I = \frac{CV}{T}$$

$$f \cdot C \cdot V_{swing}$$

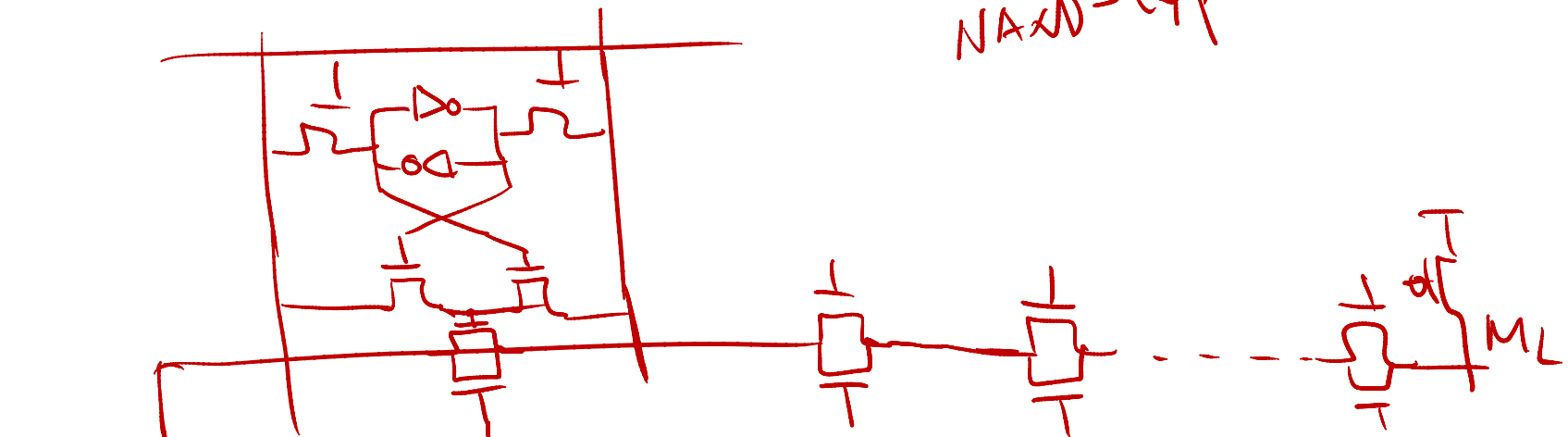


$$P \propto \left[\beta \right] \frac{f \cdot C \cdot V_{swing} V_{dd}}{f \cdot C \cdot V_{th}}$$



short-circuit path

NAND-type TCAM cell



1 word has w bits
 \Rightarrow NAND $\rightarrow \frac{1}{2^w}$
 NOR $\rightarrow \frac{1}{2}$

discharge probability
 NAND — { Low-power
 Long delay
 NOR — { high power
 high speed

[illegible]